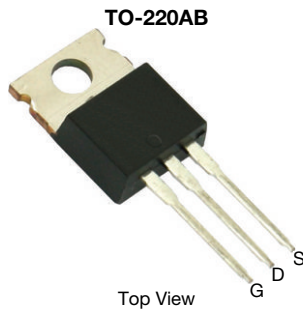


## N-Channel 200 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
$V_{DS}$ (V)	200
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10$ V	0.0152
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 7.5$ V	0.0169
$Q_g$ typ. (nC)	58
$I_D$ (A)	90
Configuration	Single

### FEATURES

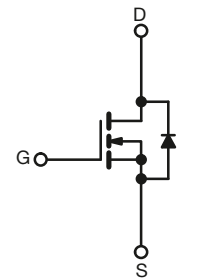
- ThunderFET® power MOSFET
- Tuned for the lowest  $R_{DS} - Q_{oss}$  FOM
- Maximum 175 °C junction temperature
- 100 %  $R_g$  and UIS tested
- Material categorization:  
for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Power supplies:
  - Uninterruptible power supplies
  - AC/DC switch-mode power supplies
  - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Solar micro inverter
- Class D audio amplifier



N-Channel MOSFET

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free and halogen-free	SUP90142E-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	200	V
Gate-source voltage	$V_{GS}$	$\pm 20$	
Continuous drain current	$I_D$	$T_C = 25$ °C	90
		$T_C = 125$ °C	52
Pulsed drain current ( $t = 100$ $\mu$ s)	$I_{DM}$	240	A
Continuous source-drain diode current	$I_S$	90	
Single pulse avalanche current <sup>a</sup>	$I_{AS}$	60	mJ
Single pulse avalanche energy <sup>a</sup>			
Maximum power dissipation	$P_D$	$T_C = 25$ °C	375 <sup>b</sup>
		$T_C = 125$ °C	125 <sup>b</sup>
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +175	°C
Soldering recommendations (peak temperature) <sup>c</sup>		260	

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	MAXIMUM	UNIT
Maximum junction-to-ambient (PCB mount) <sup>c</sup>	$R_{thJA}$	40	°C/W
Maximum junction-to-case (drain)	Steady state $R_{thJC}$	0.4	

#### Notes

- Duty cycle  $\leq 1$  %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).
- Package limited.



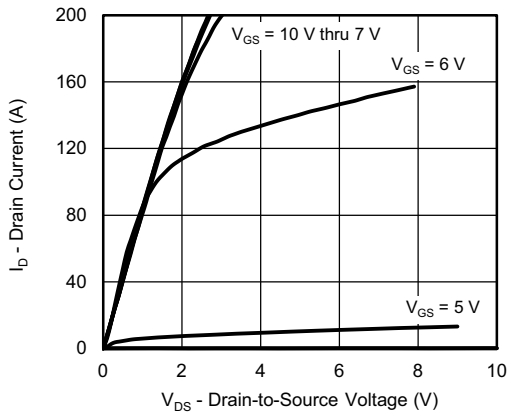
SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	200	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	-	4	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	-	-	250	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V	-	-	1	μA
		V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	150	
		V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C	-	-	5	mA
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 10 V, V <sub>GS</sub> = 10 V	60	-	-	A
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A	-	0.0126	0.0152	Ω
		V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 30 A	-	0.0133	0.0169	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A	-	63	-	S
<b>Dynamic<sup>b</sup></b>						
Input capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	3120	-	pF
Output capacitance	C <sub>OSS</sub>		-	280	-	
Reverse transfer capacitance	C <sub>rSS</sub>		-	24	-	
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 60 A	-	58	87	nC
Gate-source charge	Q <sub>gs</sub>		-	17.6	-	
Gate-drain charge	Q <sub>gd</sub>		-	17.2	-	
Output charge	Q <sub>OSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	-	108	162	
Gate resistance	R <sub>g</sub>	f = 1 MHz	1.5	3	5	Ω
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 100 V, R <sub>L</sub> = 1.66 Ω, I <sub>D</sub> ≅ 60 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	14	28	ns
Rise time	t <sub>r</sub>		-	125	250	
Turn-off delay time	t <sub>d(off)</sub>		-	27	54	
Fall time	t <sub>f</sub>		-	80	150	
<b>Drain-Source Body Diode Characteristics</b>						
Pulse diode forward current (t = 100 μs)	I <sub>SM</sub>		-	-	240	A
Body diode voltage	V <sub>SD</sub>	I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0 V	-	0.85	1.5	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 30 A, dI/dt = 100 A/μs	-	150	300	ns
Body diode reverse recovery charge	Q <sub>rr</sub>		-	0.9	1.8	nC
Reverse recovery fall time	t <sub>a</sub>		-	125	-	ns
Reverse recovery rise time	t <sub>b</sub>		-	25	-	
Body diode peak reverse recovery charge	I <sub>RM(REC)</sub>		-	11.5	20	A

**Notes**

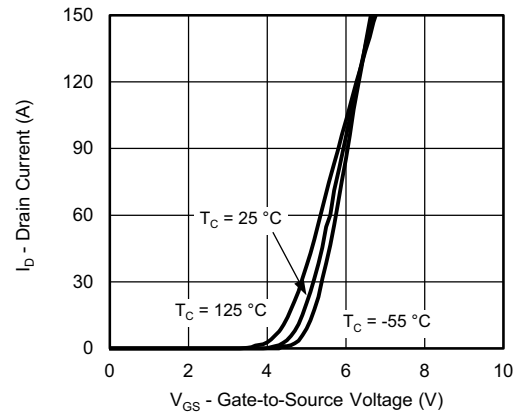
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

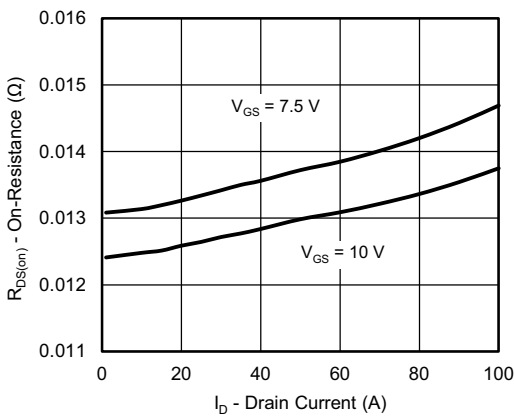
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



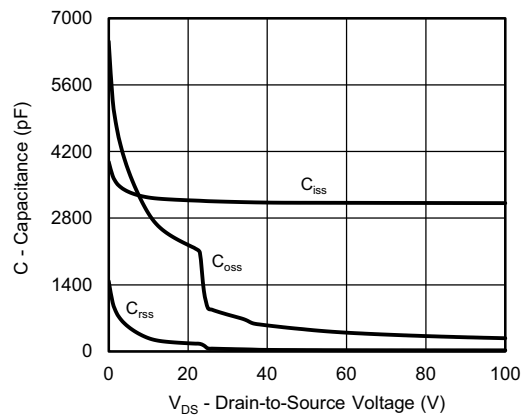
**Output Characteristics**



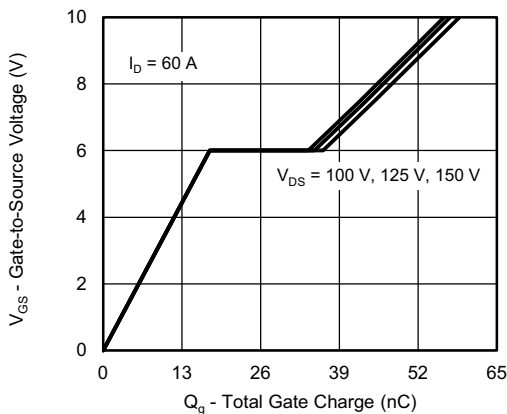
**Transfer Characteristics**



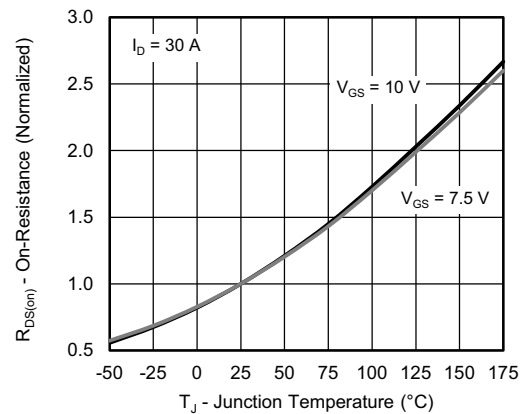
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**



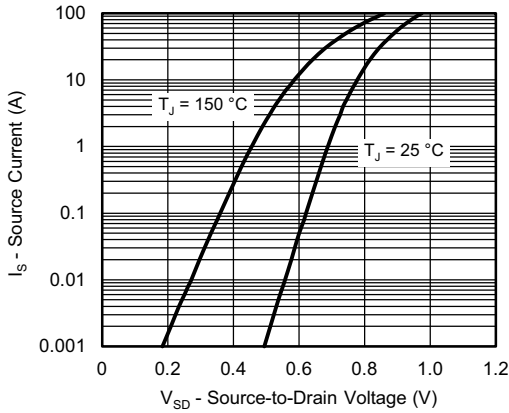
**Gate Charge**



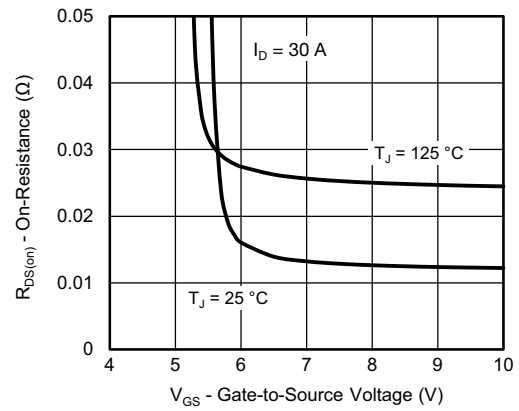
**On-Resistance vs. Junction Temperature**



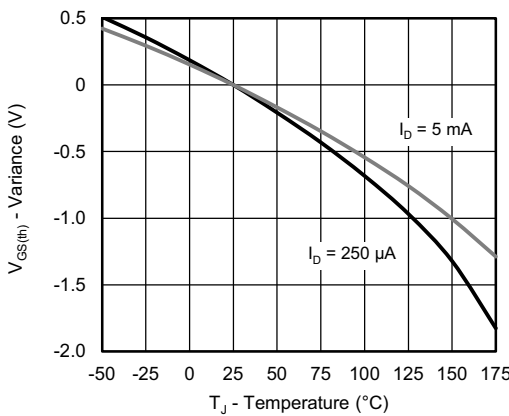
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



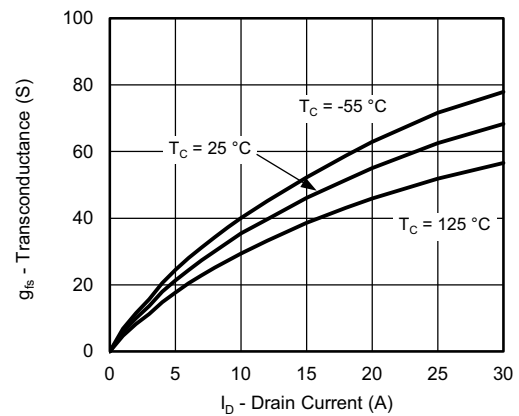
Source-Drain Diode Forward Voltage



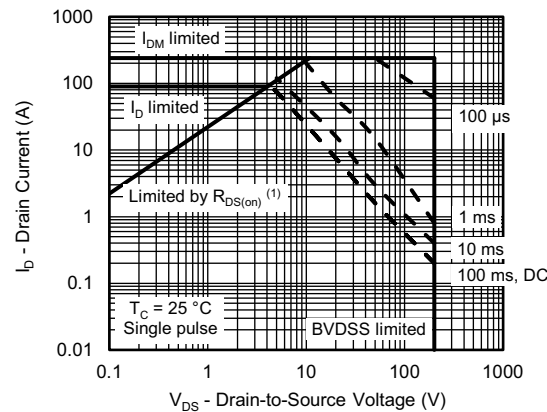
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



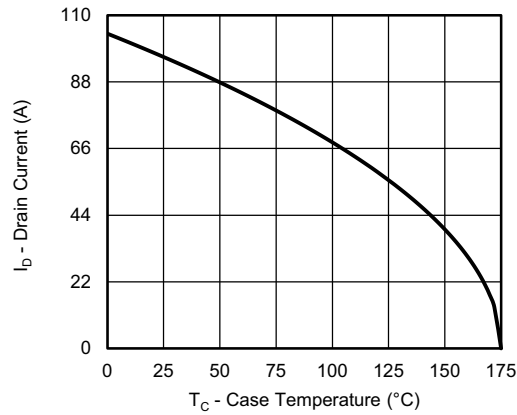
Transconductance



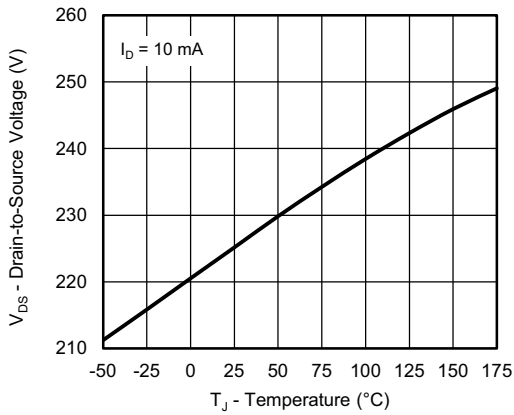
Safe Operating Area, Junction-to-Ambient



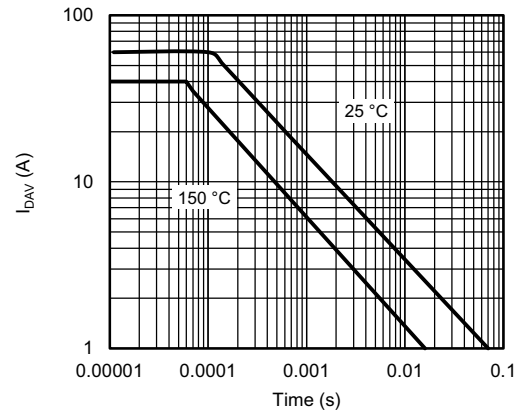
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating <sup>a</sup>



Drain Source Breakdown vs. Junction Temperature



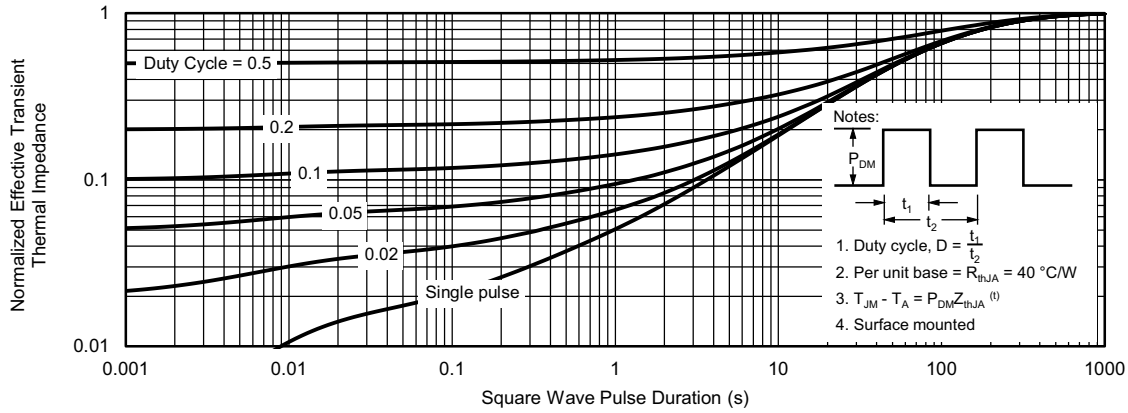
$I_{DAV}$  vs. Time

Note

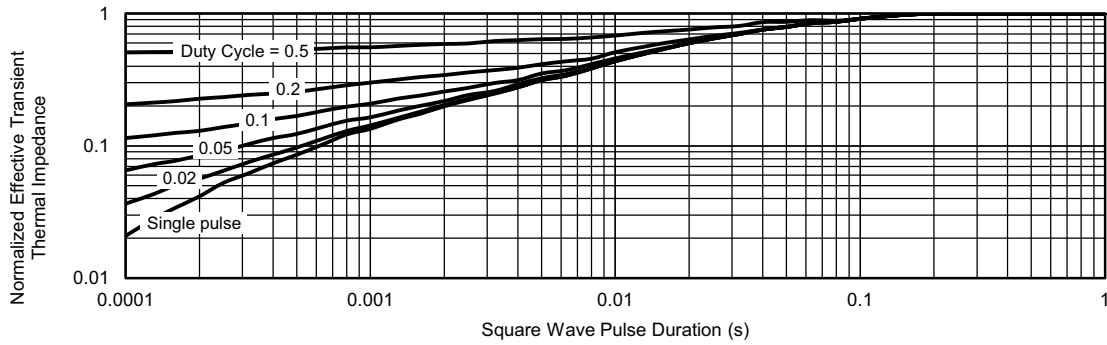
- a. The power dissipation  $P_D$  is based on  $T_J$  max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?75002](http://www.vishay.com/ppg?75002).



## **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Компания «Океан Электроники» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



## JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели, кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



Телефон: 8 (812) 309-75-97 (многоканальный)

Факс: 8 (812) 320-03-32

Электронная почта: [ocean@oceanchips.ru](mailto:ocean@oceanchips.ru)

Web: <http://oceanchips.ru/>

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, д. 2, корп. 4, лит. А